University of Central Florida







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Adaptive Behavioral Simulation Framework for 2-Terminal MTJ-based Analog to Digital Converter

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"Cross-layer Adaptive Rate/Resolution Design for Energy-Aware Acquisition of Spectrally Sparse Signals Leveraging Spin-based Devices"

- Develop energy-efficient adaptive framework to acquire spectrally-sparse signals
- Integrate adaptive quantized Compressive Sensing w/ beyond-CMOS devices





Three Pathways to Educational Impacts

Research Expertise ↔ REU Experiences ↔ High School Outreach

Spíntroníc Educational Símulation





REU Graduates / Students



Soheil Salehi, Ph.D. Completed Ph.D.; now a Post-Doctoral Researcher at UC-Davis



Adrian Tatulian, M.S. Doctoral Student

2) Mentor Impactful REU Experiences



Gustavo Camero Completed REU; now a Doctoral Student at Carnegie Mellon Univ.



Adedoyin Adepegba REU currently interning at Intel



Paul Wood REU currently interning at Intel



Daniel C. Mulvaney REU currently interning at L3-Harris



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Creating

Educational

Outreach

for High

Schoolers

Three Pathways to Educational Impacts

Research Expertise ↔ REU Experiences ↔ High School Outreach

Spíntroníc Educatíonal Símulatíon

Outreach Goals & Approach

- Mentor U/G's via NSF REU supplement
- Paid REUs conducted lit surveys of signal encoding/conversion, performed SPICE simulations w/ MTJ circuits designed by GRAs
- REUs learned SPICE circuit modeling tools via structured examples, and practived proofreading of articles composed by team members, post-CMOS technical knowledge and authoring skills





Spintronic Simulation Website

- Simulation Framework is an educational resource site companion to distribute the interactive tool to provide insights of the modeled Spin-based ADC
- Broad dissemination through web-based framework to maximize the impact of outreach





- / There is a need for low-complexity, ultra-low-power circuit for signal conversion for IoT applications
 - There is a demand for Compressive Sensing solutions that consider hardware constraints and signal constraints for IoT intelligent sampling and edge processing





Research Motivation

Need for CS solutions considering device-level constraints for IoT¹

Spíntroníc Educatíonal Símulatíon

- Maximize signal sensing and reconstruction performance while reducing energy consumption for IoT applications
- Compressive Sensing reduces number of samples per frame to decrease energy, storage, and data transmission overheads
- Non-uniform CS in hardware requires Random Number Generator (RNG)
 - True RNGs vs. Pseudo RNGs





Spin Devices in Reconfigurable Fabrics Time & Space Co-design of Digital, Analog, Storage

Spintronic Educational Simulation



- Magnetic tunnel junctions (MTJs) consist of a tunneling oxide layer sandwiched between two ferromagnetic layers.
- Magnetization of free layer can be modified using a current or voltage.
- Low-barrier MTJ can be used to build Magnetic Random Access Memory (MRAM)-based p-bit with stochastic switching capability

https://www.theregister.co.uk/20 19/03/08/samsung_mram/





https://www.everspin.com/spintransfer-torque-mram-products

- **Advantages**
- Near-zero standby power
- Area efficient
- Fast read operation
- True randomness

Everspin & IBM MTJ-based SSD and DRAM replacement products available

Intel now delivering embedded MRAM (eMRAM) in a 1T1MTJ architecture in

conjunction with their 22-nm FinFET

Toshiba is fabricating SHE-MTJ²

technology libraries¹

- 1. Wei, Liqiong, Juan G. Alzate, Umut Arslan, et al. "13.3 A 7Mb STT-MRAM in 22FFL FinFET Technology with 4ns Read Sensing Time at 0.9 V Using Write-Verify-Write Scheme and Offset-Cancellation Sensing Technique." In 2019 IEEE International Solid-State Circuits Conference-(ISSCC), pp. 214-216, 2019.
- 2. H. Yoda et al., "High-Speed Voltage-Control Spintronics Memory (High-Speed VoCSM)," 2017 IEEE International Memory Workshop (IMW), Monterey, CA, slide 7 2017, pp. 1-4.



Spintronic Educational Simulation

Voltage-Controlled Magnetic Anisotropy Magnetic Tunnel Junction (VCMA-MTJ) AIQ

- 1) During Reset step: all active VCMA-MTJs are reset to Parallel state
- 2) During Sampling step: based on determined SR and QR, first bias voltage, V_b, is applied across the active VCMA-MTJs to modify energy barrier followed by analog input, e(t), to write into the active VCMA-MTJs
- 3) During Read step: use a sense amplifier to read data stored in each VCMA-MTJ



1. S. Salehi, M. Mashhadi, A. Zaeemzadeh, N. Rahnavard, and R. F. DeMara, IEEE JETCAS-2018



Spintronic Educational Simulation

Functionalities of proposed Simulation Framework:

- Proposed Interactive Simulator provides a Graphical User Interface (GUI) that allows for the modification and insertion of values for Spin-ADC simulations
- Default parameter values reflect simulation cases used in [S. Salehi, et al., 2018]²
- Vary device parameters for running different simulations with different scenarios
- Run option that compiles all parameters and simulation options to display simulation results
- Simulation results are displayed in a different GUI window displaying different characteristics
- Help option that redirects to various educational resources site for more information



^{1.} G. Camero, S. Salehi, and R. F. DeMara, IEEE ReConfig-2019.

^{2.} S. Salehi, M. Mashhadi, A. Zaeemzadeh, N. Rahnavard, and R. F. DeMara, IEEE JETCAS-2018

^{3.} This work is funded by NSF-ECCS #1810256



Adaptive & Interactive Framework

AIQ Simulation Framework^{1,2,3}





Sample Output Waveforms:

- (a) Depicts energy consumed for each sample
- (b) Illustrates energy consumed by each MTJ
- (c) Shows Magnetization Orientation of each MTJ
- (d) Demonstrates analog input waveform
- (e) Visualizes Sampling Rate





1. G. Camero, S. Salehi, and R. F. DeMara, IEEE ReConfig-2019.

2. S. Salehi, M. Mashhadi, A. Zaeemzadeh, N. Rahnavard, and R. F. DeMara, IEEE JETCAS-2018

3. This work is funded by NSF-ECCS #1810256



Educational Outreach Goals

CCSS Website¹

Outreach Objectives:

- Utilize research findings in undergraduate & graduate coursework.
- Develop an interactive tool based on research findings.
- Utilize the proposed tool to engage and attract high school students into STEM-related fields.
- Use educational resources website for explanation and distribution of the proposed interactive tool.

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| NSF Communications, Ci | rcuits an | d Sensing | Systems | |
| Educational Resources | | | | |
| Spin-ADC Interactive Simulator | | | | |
| Download HERE SAI-Sim provides a graphical user interface (GUI) that allows for the mod Default parameter values already for simulation purposes based on JETCA Control over various simulation options and device parameters for running Simulation results are displayed in a different GUI window displaying diff | dification and insertion AS paper featured on th g different simulations ferent characteristics. | of values for Spin-ADC S is site. with different scenarios. | imulations. | |
| Tutorials | | | | |
| 🕒 YouTube | | | | |
| Paper Resources | | | | |
| Spin-ADC Interactive Simulator was based on the following research paper | ers: | | | |
| S. Salehi, M. Boloursaz Mashhadi, A. Zaeemzadeh, N. Rahnavard, and Spectrally Sparse Signals Leveraging VCMA-MTJ Devices," <i>IEEE</i> [pdf] | d R. F. DeMara " Enerş E Journal on Emerging | gy-Aware Adaptive Rate a and Selected Topics in Cir | and Resolution Sampling or rcuits and Systems (JETCAS) | of), |
| 2. S. Salehi, A. Zaeemzadeh, A. Tatulian, N. Rahnavard and R. F. DeMar of Sparse Signals in IoT Applications," accepted to appear in Procee Florida, USA, July 15-17, 2019. | ra, "MRAM-based Sto edings of IEEE Comput | chastic Oscillators for A er Society Annual Sympos | daptive Non-Uniform Sam ium on VLSI (ISVSLI'19), M | p ling liami, |
| 3. S. Salehi, R. Zand, A. Zaeemzadeh, N. Rahnavard and R. F. DeMara, ' | "AQuRate: MRAM-b | ased Stochastic Oscillato | or for Adaptive Quantizatio | on Rate |

Current Work:

- Youtube Tutorial Video: Simulation Runs with 2-Terminal MTJs
- Youtube Tutorial Video: MTJ Parameters Walkthrough
- Finalize the export option to save the acquired data from simulations in a spreadsheet document

2. S. Salehi, M. Mashhadi, A. Zaeemzadeh, N. Rahnavard, and R. F. DeMara, IEEE JETCAS-2018

^{1.} G. Camero, S. Salehi, and R. F. DeMara, IEEE ReConfig-2019.

^{3.} This work is funded by NSF-ECCS #1810256



Spintronic Simulation Framework



For more information regarding the presented simulation tool, please contact us at: https://cal.ucf.edu/ccss



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